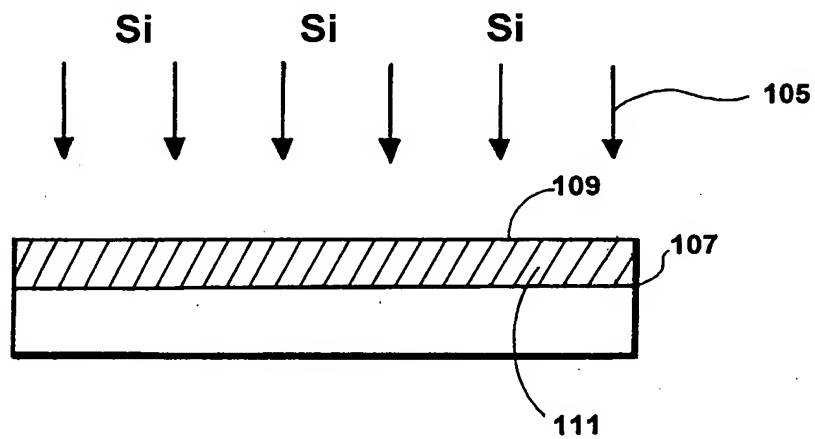
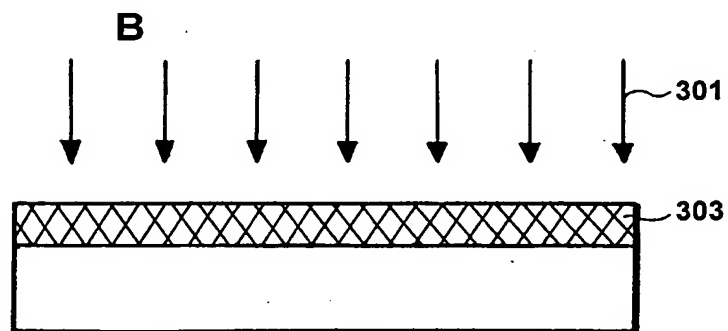


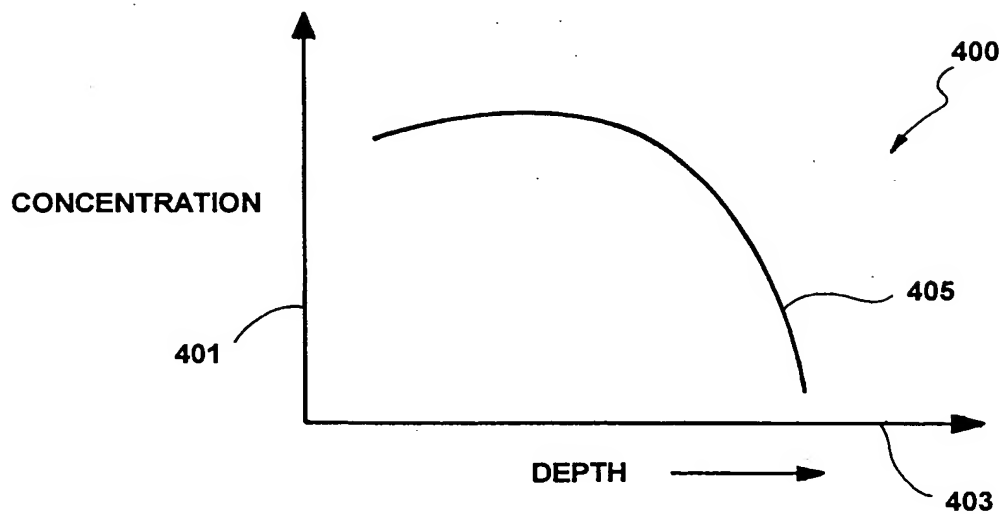
**FIG. 1**



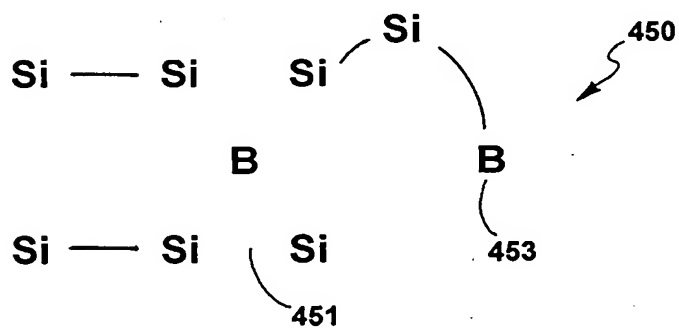
**FIG. 2**



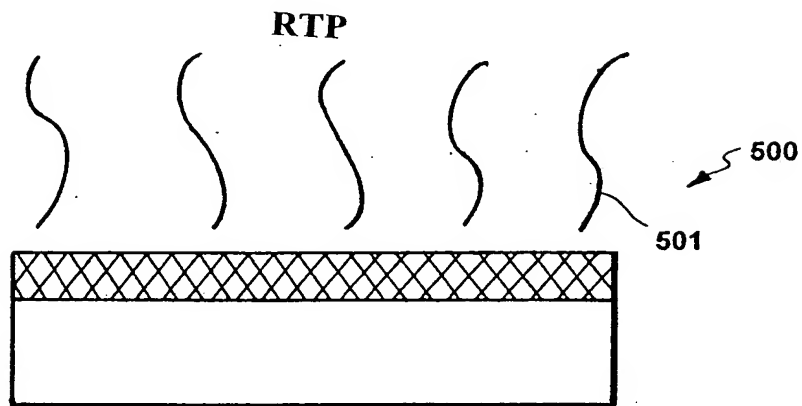
**FIG. 3**



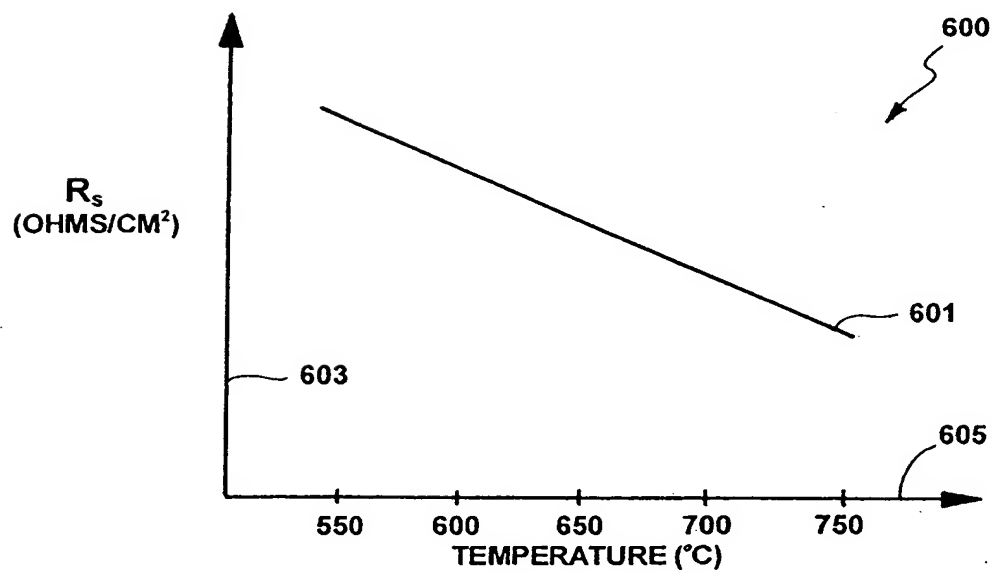
**FIG. 4**



**FIG. 4A**

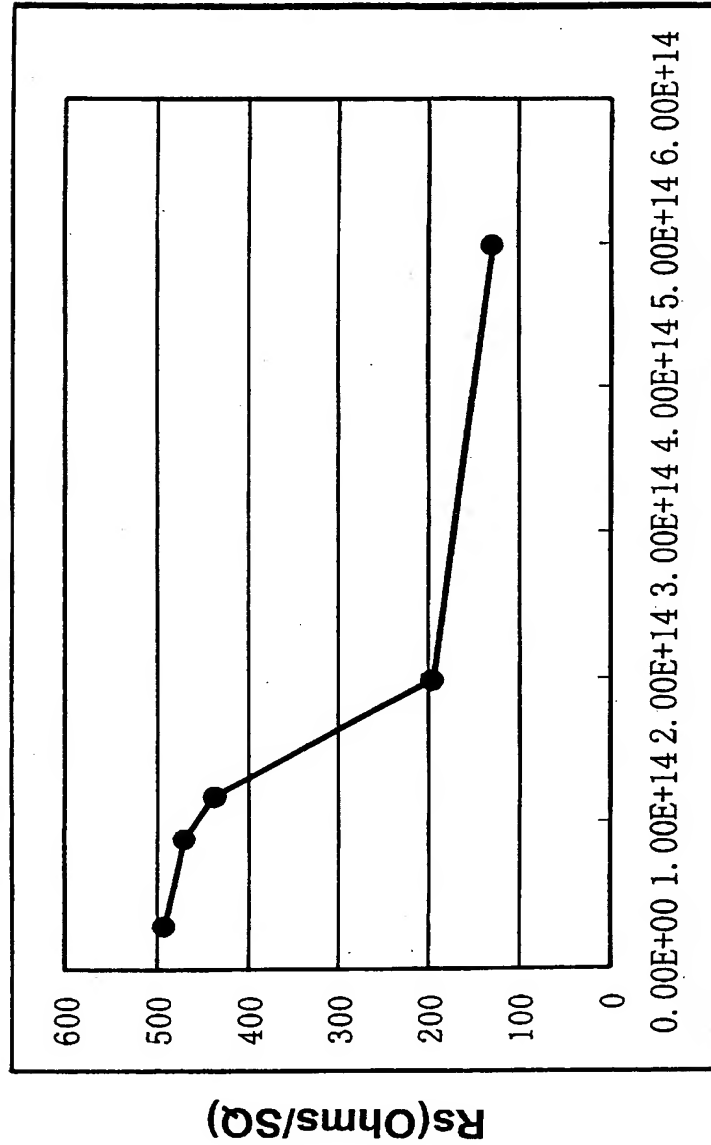


**FIG. 5**



**FIG. 6**

## Low temperature monitor



Dosage(atom/cm<sup>2</sup>)

Figure 7: Changes of Rs as a function of implant dosage of silicon,  
Boron dosage unchanged(3.5E15).

FIG. 7

## Low temperature monitor

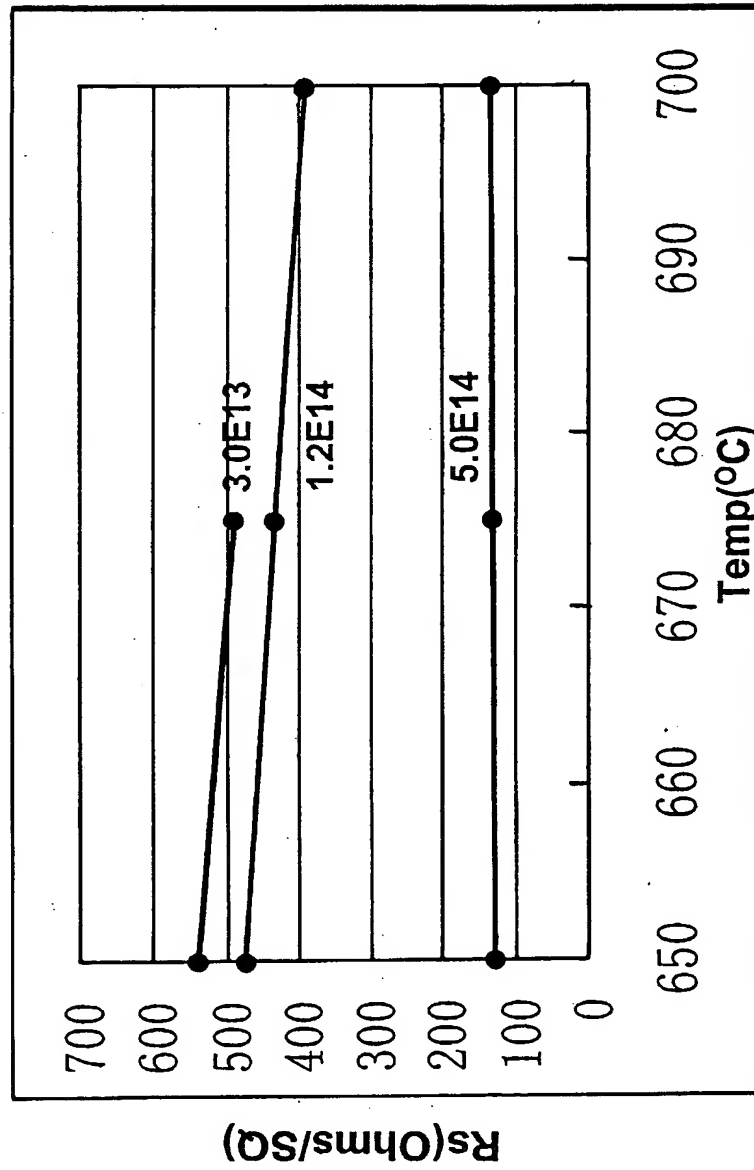


Figure 8: The dependence of  $R_s$  on annealing temperature. The implant dose of silicon varied from  $3.0E13$  to  $5.0E14$ , Boron dosage unchanged ( $3.5E15$ ).

FIG. 8